Amendments to the Claims:

Cancel Claims 1-18 without prejudice or disclaimer of the subject matter contained therein.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-18. (Canceled)

19. (New) A method of fabricating a fluid ejection device, comprising: fabricating a thinfilm structure on a device substrate;

forming a peripheral break trench structure in a first surface of the substrate circumscribing a region in which a feed slot is to be formed through the substrate;

subsequently abrasively machining the substrate from a second surface of the substrate to the break trench structure to form the feed slot.

- 20. (New) The method of Claim 19 further comprising;
- applying a barrier layer to the thinfilm structure after forming the break trench structure and before abrasively machining the substrate.
- 21. (New) The method of Claim 19 wherein said fabricating the thinfilm structure includes fabricating the thinfilm structure on said first surface of the substrate.
- 22. (New) The method of Claim 19 wherein said forming a break trench structure includes anisotropically etching the trench during a wet etch process.

23. (New) The method of Claim 19, further including:

forming a guide break trench in said first surface within the peripheral break trench structure.

- 24. (New) The method of Claim 23, wherein said guide break trench structure is formed to a depth deeper than a depth of said peripheral break trench structure.
- 25. (New) The method of Claim 24, wherein the guide break trench structure is formed with a trench width greater than a width of said peripheral break trench structure.
- 26. (New) The method of Claim 19, wherein the substrate is a silicon substrate, and wherein said forming a break trench structure includes:

etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

- 27. (New) A fluid ejection device produced by the method of Claim 19.
- 28. (New) A method of fabricating a fluid ejection device, comprising: fabricating a thinfilm structure on a device substrate;

forming a break trench structure in a first surface of the substrate, said structure comprising a plurality of small break trenches arranged along a slot axis;

subsequently abrasively machining the substrate from a second surface of the substrate to the plurality of break trenches to form a plurality of small feed slots through the substrate.

29. (New) The method of Claim 28, further comprising: defining a plurality of small substrate islands in areas separating the small slots. 30. (New) The method of Claim 29, wherein said defining a plurality of small substrate islands comprises:

forming a mask structure defining the islands;

etching the first surface through the mask structure to define the plurality of small substrate islands.

31. (New) The method of Claim 28, wherein said substrate is a silicon substrate, and wherein said forming a break trench structure includes:

etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

- 32. (New) A fluid ejection device produced by the method of Claim 28.
- 33. (New) A method of fabricating a fluid ejection device, comprising: fabricating a thinfilm structure on a substrate wafer for a plurality of fluid ejection devices to be formed on the wafer;

for each printhead to be formed, forming a peripheral break trench structure in a first surface of the substrate circumscribing a region in which a feed slot is to be formed through the substrate for each fluid ejection device to be formed on the wafer:

applying a barrier layer to the thinfilm structure;

subsequently abrasively machining the wafer from a second surface of the substrate to the peripheral break trench structure to form the feed slot for each fluid ejection device to be formed on the wafer;

attaching an orifice plate structure for each fluid ejection device to be formed on the wafer:

sawing the wafer to separate individual fluid ejection devices; and attaching the fluid ejection devices to device circuitry.